

Medium power transistor (−32V, −2A)

2SB1188 / 2SB1182 / 2SB1240

● **Features**

1) Low $V_{CE(sat)}$.

$$V_{CE(sat)} = -0.5V \text{ (Typ.)}$$

$$(I_C/I_B = -2A / -0.2A)$$

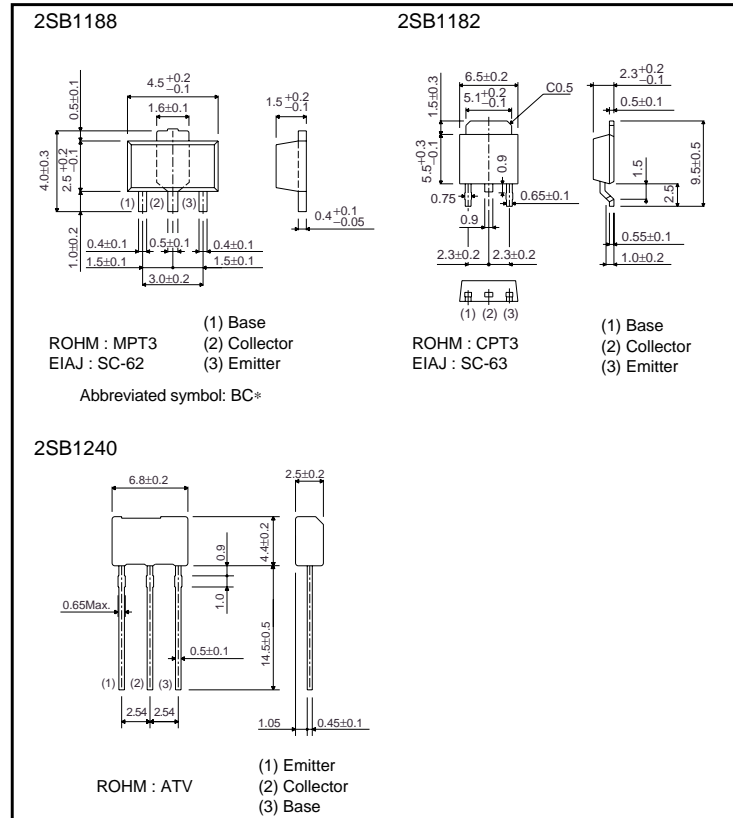
2) Complements the 2SD1766 / 2SD1758 / 2SD1862

● **Structure**

Epitaxial planar type

PNP silicon transistor

● **External dimensions (Units : mm)**



* Denotes hFE

● **Absolute maximum ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	−40	V
Collector-emitter voltage	V_{CEO}	−32	V
Emitter-base voltage	V_{EBO}	−5	V
Collector current	I_C	−2	A(DC)
		−3	A(Pulse) *1
Collector power dissipation	P_C	0.5	W
		2	W *2
		10	W(Tc=25°C)
		1	W *3
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55~+150	°C

*1 Single pulse, Pw=100ms

*2 When mounted on a 40×40×0.7 mm ceramic board.

*3 Printed circuit board, 1.7mm thick, collector copper plating 100mm² or larger.

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	-40	-	-	V	I _C =-50μA
Collector-emitter breakdown voltage	BV _{CEO}	-32	-	-	V	I _C =-1mA
Emitter-base breakdown voltage	BV _{EBO}	-5	-	-	V	I _E =-50μA
Collector cutoff current	I _{CBO}	-	-	-1	μA	V _{CB} =-20V
Emitter cutoff current	I _{EBO}	-	-	-1	μA	V _{EB} =-4V
Collector-emitter saturation voltage	V _{CE(sat)}	-	-0.5	-0.8	V	I _C /I _B =-2A/-0.2A
DC current transfer ratio	h _{FE}	82	-	390	-	V _{CE} =-3V, I _C =-0.5A
Transition frequency	f _T	-	100	-	MHz	V _{CE} =-5V, I _E =0.5A, f=30MHz
Output capacitance	C _{ob}	-	50	-	pF	V _{CB} =-10V, I _E =0A, f=1MHz

* Measured using pulse current.

●Packaging specifications and h_{FE}

Type	h _{FE}	Package	Taping		
		Code	T100	TL	TV2
		Basic ordering unit (pieces)	1000	2500	2500
2SB1188	PQR	○	-	-	-
2SB1182	PQR	-	○	-	-
2SB1240	PQR	-	-	○	-

h_{FE} values are classified as follows :

Item	P	Q	R
h _{FE}	82~180	120~270	180~390

●Electrical characteristic curves

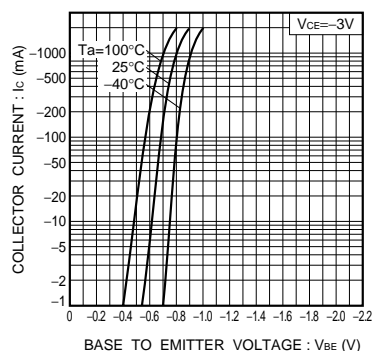


Fig.1 Grounded emitter propagation characteristics

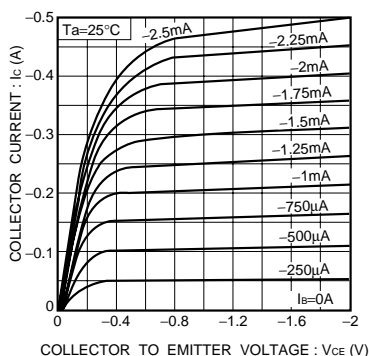


Fig.2 Grounded emitter output characteristics

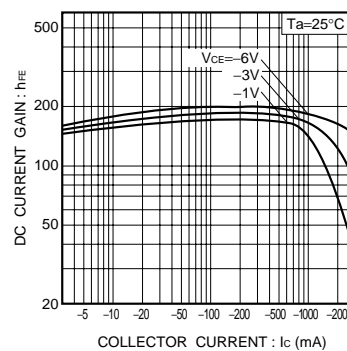


Fig.3 DC current gain vs. collector current (I)

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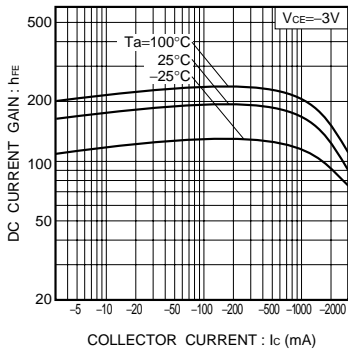


Fig.4 DC current gain vs. collector current (II)

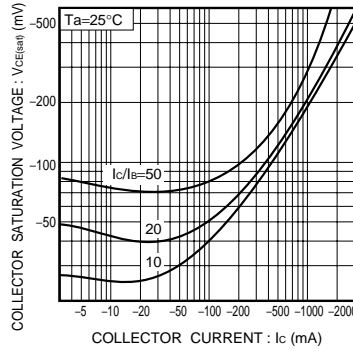


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

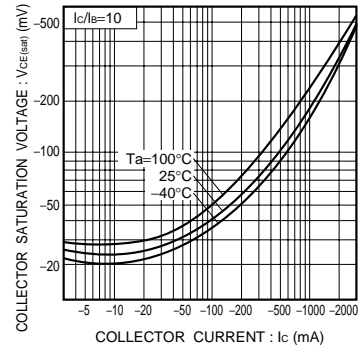


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

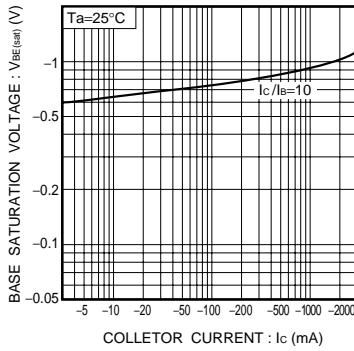


Fig.7 Base-emitter saturation voltage vs. collector current

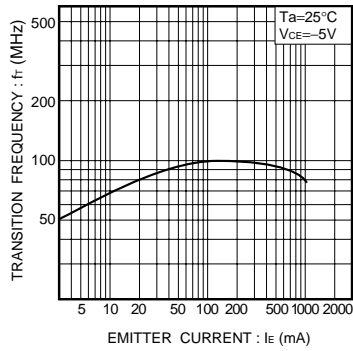


Fig.8 Gain bandwidth product vs. emitter current

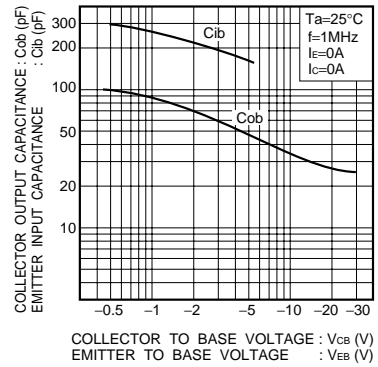


Fig.9 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

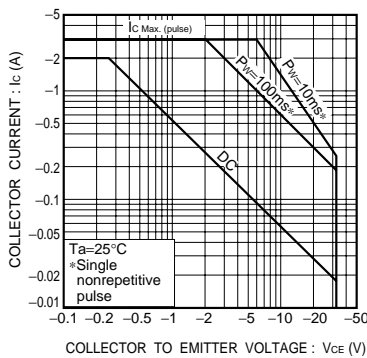


Fig.10 Safe operation area (2SB1188)

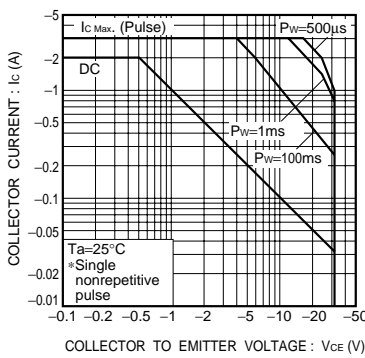


Fig.11 Safe operation area (2SB1182)